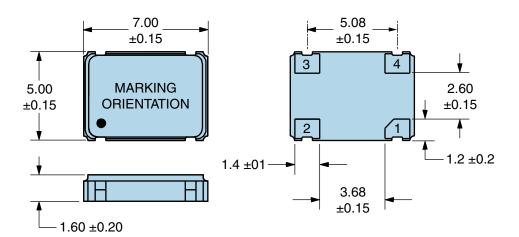


| ELECTRICAL SPECIFICATIONS | | |
|---------------------------------------|--|--|
| Nominal Frequency | 12.000MHz | |
| Frequency Tolerance/Stability | ±100ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C, Shock, and Vibration) | |
| Aging at 25°C | ±5ppm/year Maximum | |
| Operating Temperature Range | -10°C to +70°C | |
| Supply Voltage | 5.0Vdc ±10% | |
| Input Current | 10mA Maximum (No Load) | |
| Output Voltage Logic High (Voh) | 2.4Vdc Minimum with TTL Load, Vdd-0.5Vdc Minimum with HCMOS Load | |
| Input Current Logic High (Ioh) | -4mA | |
| Output Voltage Logic Low (Vol) | 0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load | |
| Input Current Logic Low (IoI) | 4mA | |
| Rise/Fall Time | 10nSec Maximum (Measured at 0.4Vdc to 2.4Vdc with TTL Load; Measured at 10% to 90% of waveform with HCMOS Load) | |
| Duty Cycle | 50 ±10(%) (Measured at 50% of waveform with HCMOS Load or at 1.4Vdc with TTL Load) | |
| Load Drive Capability | Low Drive (10LSTTL Load or 30pF HCMOS Load Maximum) | |
| Output Logic Type | CMOS | |
| Pin 1 Connection | Tri-State (High Impedance) | |
| Tri-State Input Voltage (Vih and Vil) | +2.0Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output. | |
| RMS Phase Jitter | 1pSec Maximum (12kHz to 20MHz offset frequency) | |
| Start Up Time | 10mSec Maximum | |
| Storage Temperature Range | -55°C to +125°C | |

| ENVIRONMENTAL & MECHANICAL SPECIFICATIONS | | |
|---|---------------------------------------|--|
| Fine Leak Test | MIL-STD-883, Method 1014, Condition A | |
| Gross Leak Test | MIL-STD-883, Method 1014, Condition C | |
| Mechanical Shock | MIL-STD-202, Method 213, Condition C | |
| Resistance to Soldering Heat | MIL-STD-202, Method 210 | |
| Resistance to Solvents | MIL-STD-202, Method 215 | |
| Solderability | MIL-STD-883, Method 2003 | |
| Temperature Cycling | MIL-STD-883, Method 1010 | |
| Vibration | MIL-STD-883, Method 2007, Condition A | |



MECHANICAL DIMENSIONS (all dimensions in millimeters)



| PIN | CONNECTION |
|-----|----------------|
| 1 | Tri-State |
| 2 | Ground |
| 3 | Output |
| 4 | Supply Voltage |

| LINE | MARKING |
|------|---|
| 1 | ECLIPTEK |
| 2 | 12.000M |
| 3 | XXYZZ XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year |

Suggested Solder Pad Layout

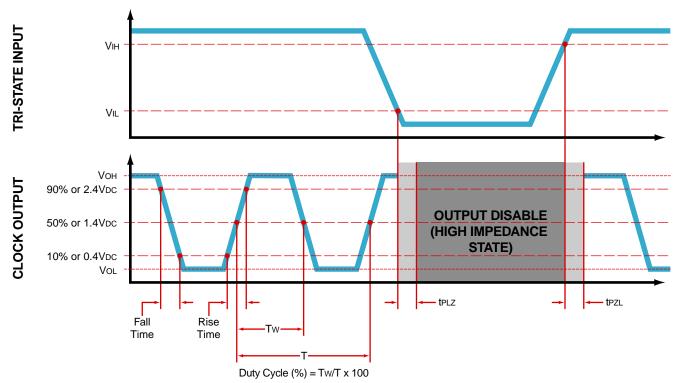
All Dimensions in Millimeters



All Tolerances are ±0.1



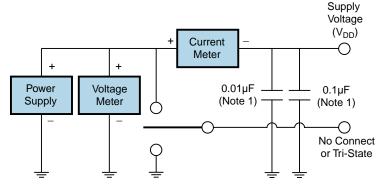
OUTPUT WAVEFORM & TIMING DIAGRAM

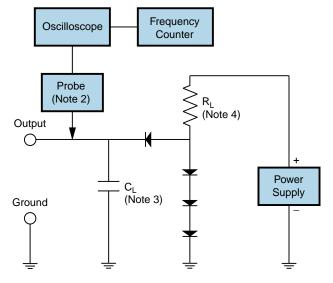


Test Circuit for TTL Output

| Output Load Drive Capability | R _L Value (Ohms) | C _L Value (pF) |
|---------------------------------|--------------------------------|------------------------------|
| 10TTL | 390 | 15 |
| 5TTL | 780 | 15 |
| 2TTL | 1100 | 6 |
| 10LSTTL | 2000 | 15 |
| 1TTL | 2200 | 3 |

Table 1: R_L Resistance Value and C_L Capacitance Value Vs. Output Load Drive Capability





Note 1: An external $0.1\mu F$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu F$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_{L} includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



Test Circuit for CMOS Output



Note 1: An external $0.1\mu\text{F}$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu\text{F}$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

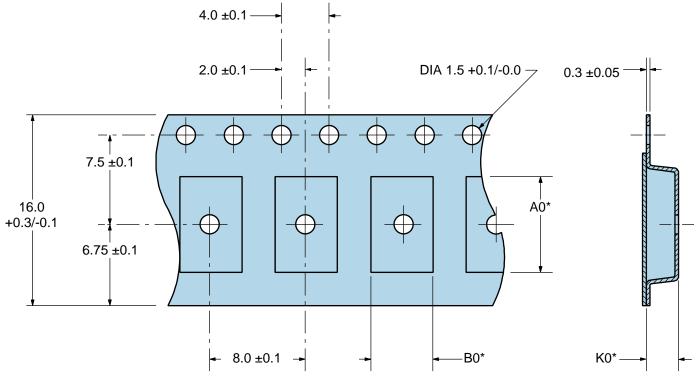
Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value \dot{C}_L includes sum of all probe and fixture capacitance.

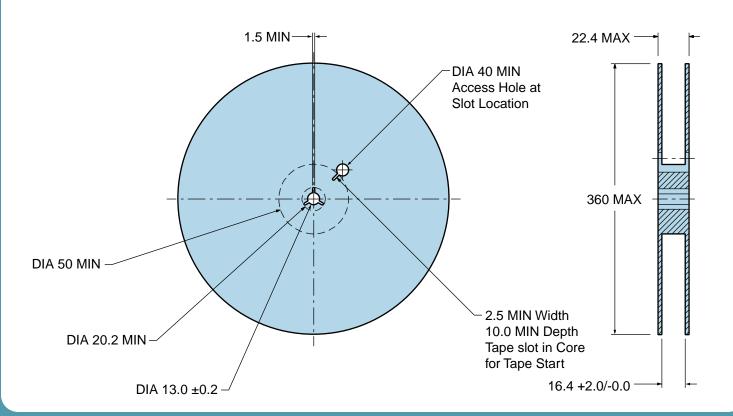


Tape & Reel Dimensions

Quantity Per Reel: 1,000 units



*Compliant to EIA 481A





Recommended Solder Reflow Methods

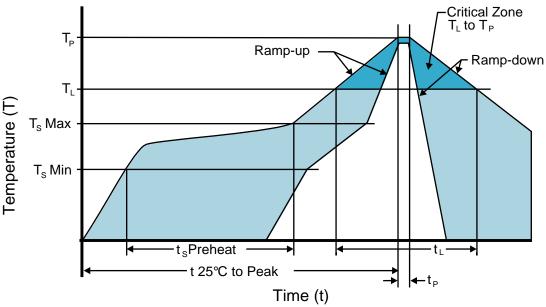


High Temperature Infrared/Convection

| 3°C/second Maximum |
|---|
| |
| 150°C |
| 175°C |
| 200°C |
| 60 - 180 Seconds |
| 3°C/second Maximum |
| |
| 217°C |
| 60 - 150 Seconds |
| 260°C Maximum for 10 Seconds Maximum |
| 250°C +0/-5°C |
| 20 - 40 seconds |
| 6°C/second Maximum |
| 8 minutes Maximum |
| Level 1 |
| Temperatures shown are applied to body of device. |
| |



Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

| T _s MAX to T _L (Ramp-up Rate) | 5°C/second Maximum |
|---|--|
| Preheat | |
| - Temperature Minimum (T _s MIN) | N/A |
| - Temperature Typical (T _s TYP) | 150°C |
| - Temperature Maximum (T _s MAX) | N/A |
| - Time (t _s MIN) | 60 - 120 Seconds |
| Ramp-up Rate (T _L to T _P) | 5°C/second Maximum |
| Time Maintained Above: | |
| - Temperature (T∟) | 150°C |
| - Time (t∟) | 200 Seconds Maximum |
| Peak Temperature (T _P) | 240°C Maximum |
| Target Peak Temperature (T _P Target) | 240°C Maximum 1 Time / 230°C Maximum 2 Times |
| Time within 5°C of actual peak (tp) | 10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time |
| Ramp-down Rate | 5°C/second Maximum |
| Time 25°C to Peak Temperature (t) | N/A |
| Moisture Sensitivity Level | Level 1 |
| Additional Notes | Temperatures shown are applied to body of device. |

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)